Silicon NPN Power Transistors 2SD234

DESCRIPTION

·With TO-220 package
·Complement to type 2SB434

APPLICATIONS

·For low frequency power amplifier
and switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

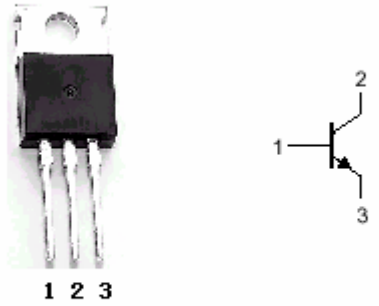

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	60	V
V_{CEO}	Collector-emitter voltage	Open base	50	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		3	A
P_C	Collector power dissipation		1.5	W
		T_C=25□	25	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=5mA ,I_B=0	50			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ,I_E=0	60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ,I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3A; I_B=0.3A			1.2	V
V_{BEsat}	Base-emitter saturation voltage	I_C=3A; I_B=0.3A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=40V; I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=4V; I_C=0			10	μA
h_{FE}	DC current gain	I_C=0.5A ; V_{CE}=1V	40		240	
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=10V,f=1MHz		90		pF
f_T	Transition frequency	I_C=0.5A ; V_{CE}=10V		3		MHz

◆ **h_{FE} Classifications**

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

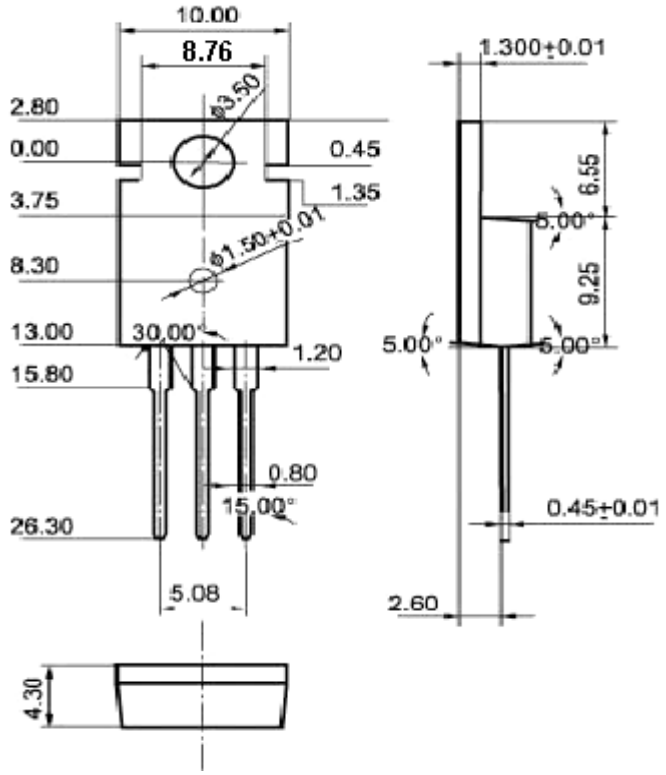

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)